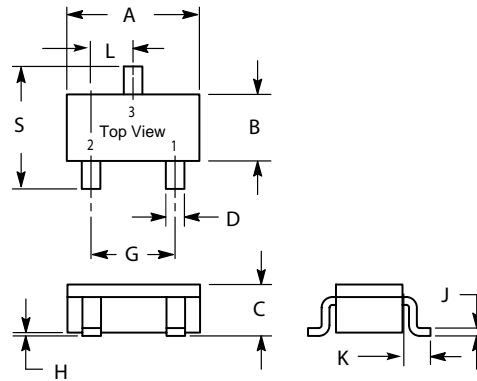


RoHS Compliant Product

A suffix of "-C" specifies halogen & lead-free

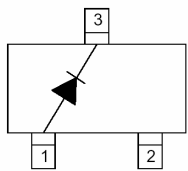
## Description

- \* The SBAS16 is designed for high-speed switching application in hybrid thick and thin-film circuits.
- \* The devices is manufactured by the silicon epitaxial planar process and packed in a plastic surface mount package.

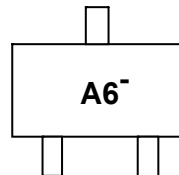


SC-59		
Dim	Min	Max
A	2.70	3.10
B	1.40	1.60
C	1.00	1.30
D	0.35	0.50
G	1.70	2.10
H	0.00	0.10
J	0.10	0.26
K	0.20	0.60
L	0.85	1.15
S	2.40	2.80
All Dimension in mm		

Diagram :



Marking



## Absolute Maximum Ratings at $T_A = 25^\circ\text{C}$

Parameter	Symbol	Ratings	Unit
Reverse Voltage	$V_R$	75	V
Repetitive Reverse Voltage	$V_{RR}$	85	V
Forward Current	$I_F$	250	mA
Repetitive Forward Current	$I_{FR}$	500	mA
Forward Surge Current (1ms)	$I_{FSM}$	1000	mW
Total Power Dissipation	$P_D$	200	mW
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-65~+150	$^\circ\text{C}$

## Characteristics at $T_A = 25^\circ\text{C}$

Characteristic	Symbol	Min.	Max.	Unit	Test Conditions
Reverse Breakdown Voltage	$V(BR)$	75	-	V	$I_R=100\mu\text{A}$
Forward Voltage	$V_F(1)$	-	715	mV	$I_F=1\text{mA}$
	$V_F(2)$	-	855	mV	$I_F=10\text{mA}$
	$V_F(3)$	-	1000	mV	$I_F=50\text{mA}$
	$V_F(4)$	-	1250	mV	$I_F=150\text{mA}$
Reverse Current	$I_R$	-	1	$\mu\text{A}$	$V_R=75\text{V}$
Total Capacitance	$C_T$		2	pF	$V_R=0, f=1\text{MHz}$
Reverse Recovery Time	$T_{rr}$	-	6	nS	$I_F=I_R=10\text{mA}, R_L=100\Omega$ measured at $I_R=1\text{mA}$

**Characteristics Curve**

